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Books

- [1] M. Sugiyama, K. Fujii and S. Nakamura (eds.), “Solar to Chemical Energy Conversion — Theory and Applications —,” Springer, ISSN 2195-1284 (2016).
- [2] M. Sugiyama, “Photovoltaic power generation.” A chapter in “Energy Technology Roadmaps of Japan —Future Energy Systems Based on Feasible Technologies Beyond 2030—,” by Y. Kato, M. Koyama, Y. Kukushima, T. Nakagaki (eds.), Springer, ISBN 978-4-431-55951-1.

International Journals

- [1] Shigekazu Okumura, Kazuki Fujisawa, Tamami Naruke, Kenichi Nishi, Yutaka Onishi, Keizo Takemasa, Mitsuru Sugawara, Masakazu Sugiyama, "Impact of low-temperature cover layer growth of InAs/GaAs quantum dots on their optical properties," Japanese Journal of Applied Physics, 61 (8) (2022/8)
- [2] Go Soma, Warakorn Yanwachirakul, Toshiki Miyazaki, Eisaku Kato, Bunta Onodera, Ryota Tanomura, Taichiro Fukui, Shota Ishimura, Masakazu Sugiyama, Yoshiaki Nakano, Takuo Tanemura, "Ultra-Broadband Surface-Normal Coherent Optical Receiver with Nanometallic Polarizers," ACS Photonics (2022/7/21)
- [3] Tatsuro Endo, Tsutomu Minegishi, Soraya Shizumi, Masakazu Sugiyama, "Ambient Sensitive Charge Transfer from GaN to Pt during a Photocatalytic Reaction," The Journal of Physical Chemistry Letters, 3978-3982 (2022/5/12)
- [4] Masahiro Sato, Yuki Imazeki, Takahito Takeda, Masaki Kobayashi, Susumu Yamamoto, Iwao Matsuda, Jun Yoshinobu, Yoshiaki Nakano, Masakazu Sugiyama, "Comparative Study of H₂O and O₂ Adsorption on the GaN Surface," The Journal of Physical Chemistry C, 125 (46) , 25807-25815 (2021/11/25)
- [5] Tetsuya Nakamura, Warakorn Yanwachirakul, Mitsuru Imaizumi, Masakazu Sugiyama, Hidefumi Akiyama, Yoshitaka Okada, "Reducing Shockley-Read-Hall recombination losses in the depletion region of a solar cell by using a wide-gap emitter layer," Journal of Applied Physics, 130 (15) (2021/10/21)
- [6] S. Okumura, K. Fujisawa, M. Yamaguchi, T. Naruke, K. Nishi, K. Takemasa, M. Sugawara, M. Sugiyama, “Impact of dislocations in InAs quantum dot with InGaAs strain-reducing layer structures on their optical properties,” Jpn. J. Appl. Phys. v 60, n 3, p 035507 (7 pp.), March (2021)
- [7] M. Asami, K. Watanabe, Y. Nakano, M. Sugiyama, “Smooth Surface Morphology and Long Carrier Lifetime of InGaP Realized by Low-Temperature-Grown Cover Layer,” Physica Status Solidi (B), v 259, n 2, February (2022)
- [8] M. Hino, M. Asami, K. Watanabe, Y. Nakano, M. Sugiyama, “Enhanced Radiative Efficiency of InGaAs/GaAsP Multiple Quantum Wells by Optimizing the Thickness of Interlayers,” Physica Status

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- [9] Y. H. Xie, Y. Ueda, M. Sugiyama, "Greedy energy management strategy and sizing method for a stand-alone microgrid with hydrogen storage," *J. Energy Storage*, vol 44, 103406, Nov. (2021)
- [10] Y. H. Xie, Y. Ueda, M. Sugiyama, "A Two-Stage Short-Term Load Forecasting Method Using Long Short-Term Memory and Multilayer Perceptron," *Energies*, vol. 14, no. 18, 5873, Sep. (2021)
- [11] Vikas Nandal, Yuriy Pihosh, Tomohiro Higashi, Tsutomu Minegishi, Taro Yamada, Kazuhiko Seki, Masakazu Sugiyama, Kazunari Domen, "Probing fundamental losses in nanostructured Ta₃N₅ photoanodes: design principles for efficient water oxidation," *Energy Environ. Sci.*, 14, 4038-4047 (2021)
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